

version, except that marked up versions are not being supplied for any canceled claim.

Please cancel claims 1-32  
*46-50*

Please add claims 33-37 as follows:

*Rule 126*  
46  
38. (New) A method of forming a bottom-gated thin film transistor comprising the following steps:

forming a transistor gate;  
forming a polycrystalline thin film transistor layer over the transistor gate;  
forming a fluorine containing layer proximate the polycrystalline thin film transistor layer; and  
transferring fluorine into the polycrystalline thin film transistor layer from the fluorine containing layer.

*21*  
*Cont*  
47  
34. (New) The method of claim 33 wherein the polycrystalline thin film transistor layer comprises silicon.

48  
35. (New) The method of claim 33 wherein the forming a fluorine containing layer comprises forming a sacrificial fluorine containing layer over the thin film transistor layer by chemical vapor deposition utilizing  $WF_6$  and  $SiH_4$  precursors.

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*Sub D17*

36. (New) The method of claim ~~33~~ further comprising, after the transferring fluorine, removing the sacrificial layer from over the thin film transistor layer.

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37. (New) A method of forming a bottom-gated thin film transistor comprising the following steps:

forming a transistor gate;

forming a polycrystalline thin film transistor layer over the transistor gate;

*C1 Cncl*

forming a fluorine containing layer over the polycrystalline thin film transistor layer;

providing a buffering layer intermediate the thin film transistor layer and the fluorine containing layer; and

transferring fluorine into the polycrystalline thin film transistor layer from the fluorine containing layer.